



STY140NS10

N-CHANNEL 100V - 0.009 Ω - 140A MAX247™ MESH OVERLAY™ POWER MOSFET

TYPE	V _{DSS}	R _{DS(on)}	I _D
STY140NS10	100V	<0.011 Ω	140A

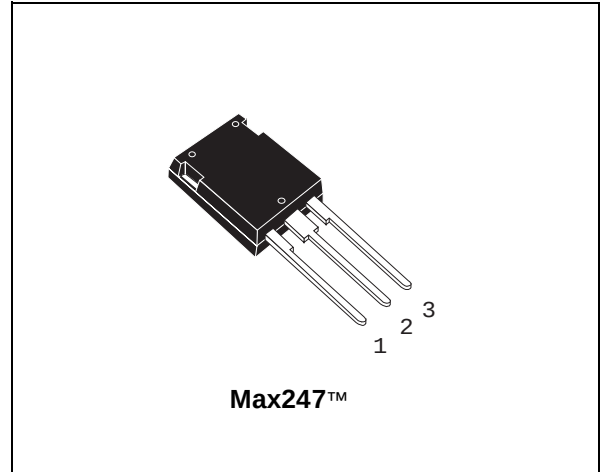
- TYPICAL R_{DS(on)} = 0.009 Ω
- STANDARD THRESHOLD DRIVE
- 100% AVALANCHE TESTED

DESCRIPTION

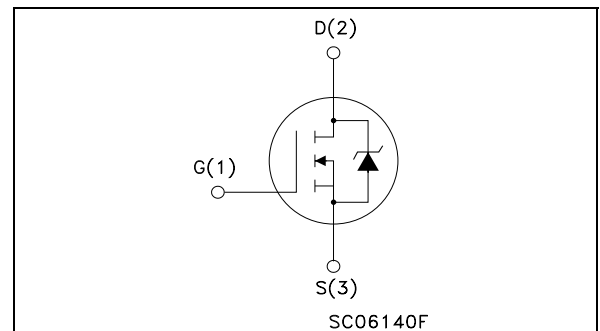
Using the latest high voltage MESH OVERLAY™ process, STMicroelectronics has designed an advanced family of power MOSFETs with outstanding performances. The new patent pending strip layout coupled with the Company's proprietary edge termination structure, gives the lowest R_{DS(on)} per area, exceptional avalanche and dv/dt capabilities and unrivalled gate charge and switching characteristics.

APPLICATIONS

- HIGH CURRENT, HIGH SWITCHING SPEED
- SWITCH MODE POWER SUPPLY (SMPS)



INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	100	V
V _{DGR}	Drain-gate Voltage (R _{GS} = 20 k Ω)	100	V
V _{GS}	Gate- source Voltage	± 20	V
I _D	Drain Current (continuous) at T _C = 25°C	140	A
I _D	Drain Current (continuous) at T _C = 100°C	99	A
I _{DM} (●)	Drain Current (pulsed)	560	A
P _{tot}	Total Dissipation at T _C = 25°C	450	W
	Derating Factor	3	W/°C
E _{AS} (1)	Single Pulse Avalanche Energy	2900	mJ
dv/dt (2)	Peak Diode Recovery voltage slope	5	V/ns
T _{stg}	Storage Temperature	-55 to 175	°C
T _j	Operating Junction Temperature	-55 to 175	°C

(●) Pulse width limited by safe operating area.

(1) Starting T_j = 25 °C, I_D = 70A, V_{DD} = 50V

(2) I_{SD} ≤ 140A, di/dt ≤ 200A/μs, V_{DD} ≤ V_{(BR)DSS}, T_j ≤ T_{JMAX}.

STY140NS10

THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-case	Max	0.33	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient	Max	30	°C/W
T _j	Maximum Lead Temperature For Soldering Purpose	Typ	300	°C

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 µA, V _{GS} = 0	100			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating T _C = 125°C			1 10	µA µA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ± 20V			±100	nA

ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} I _D = 250 µA	2		4	V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10 V I _D = 70 A		0.009	0.011	Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (*)	Forward Transconductance	V _{DS} = 20 V I _D = 70 A		50		S
C _{iss} C _{oss} C _{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	V _{DS} = 25V, f = 1 MHz, V _{GS} = 0		12600 2100 690		pF pF pF

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Delay Time Rise Time	$V_{DD} = 50\text{ V}$ $I_D = 70\text{ A}$ $R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$ (Resistive Load, Figure 1)		40 150		ns ns
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD}=50\text{V}$ $I_D=140\text{A}$ $V_{GS}=10\text{V}$ (see test circuit, Figure 2)		450 70 170	600	nC nC nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$ t_f	Turn-off Delay Time Fall Time	$V_{DD} = 50\text{ V}$ $I_D = 70\text{ A}$ $R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$ (Resistive Load, Figure 1)		465 270		ns ns

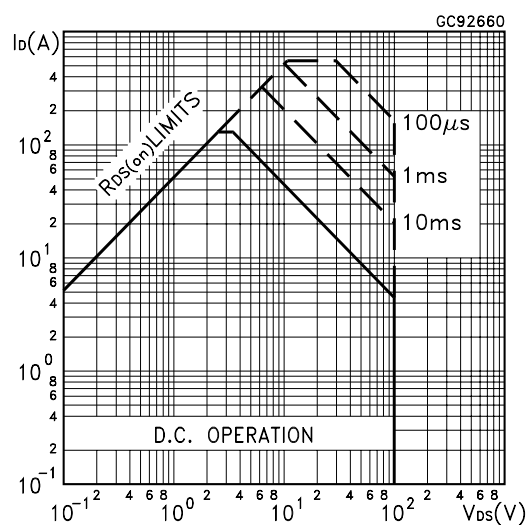
SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} $I_{SDM}(\bullet)$	Source-drain Current Source-drain Current (pulsed)				140 560	A A
$V_{SD}^(*)$	Forward On Voltage	$I_{SD} = 140\text{ A}$ $V_{GS} = 0$			1.5	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 140\text{ A}$ $di/dt = 100\text{A}/\mu\text{s}$ $V_r = 20\text{ V}$ $T_J = 150^\circ\text{C}$ (Inductive Load, Figure 3)			275 2 15	ns μC A

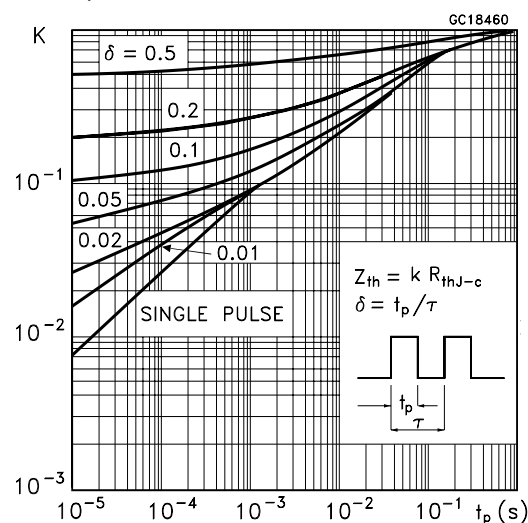
(*)Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.

($\bullet$)Pulse width limited by safe operating area.

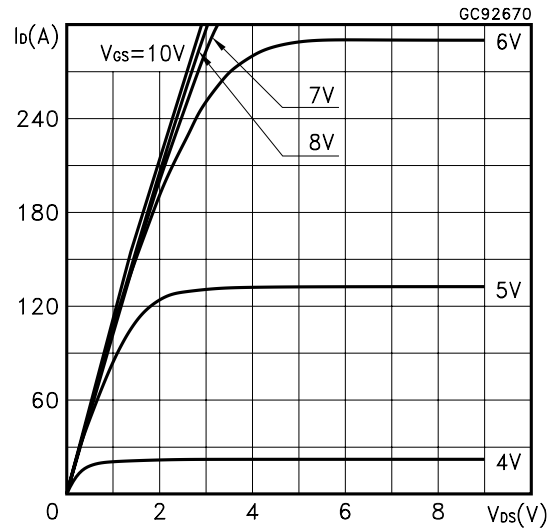
Safe Operating Area



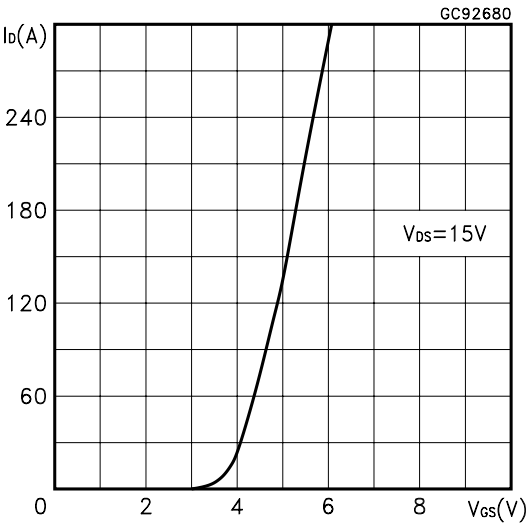
Thermal Impedance



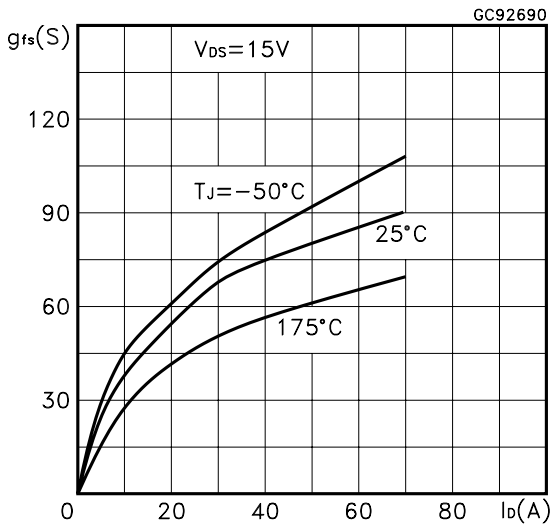
Output Characteristics



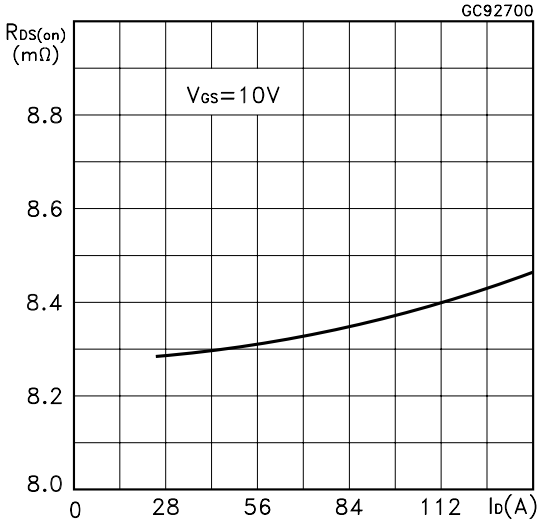
Transfer Characteristics



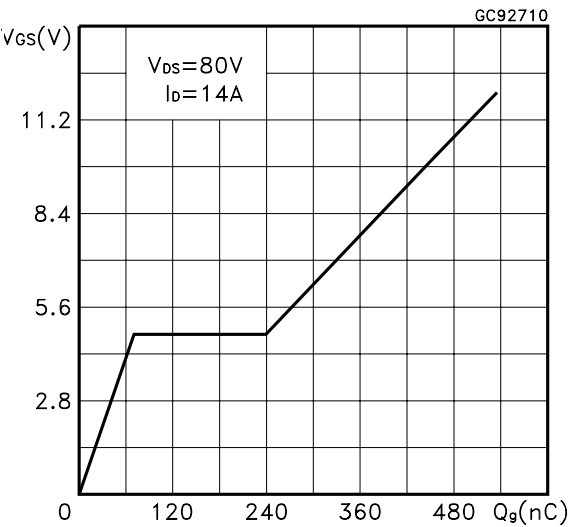
Transconductance



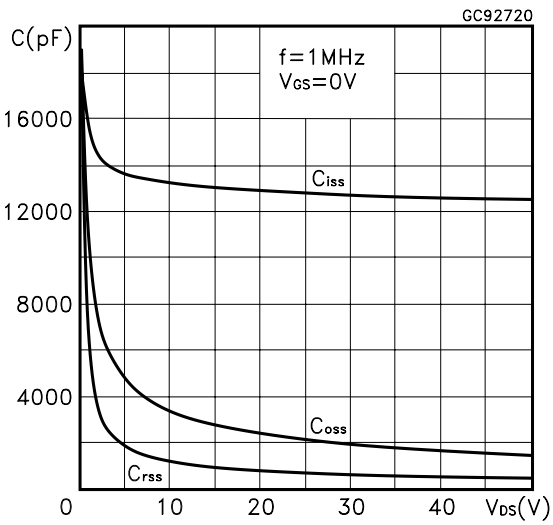
Static Drain-source On Resistance



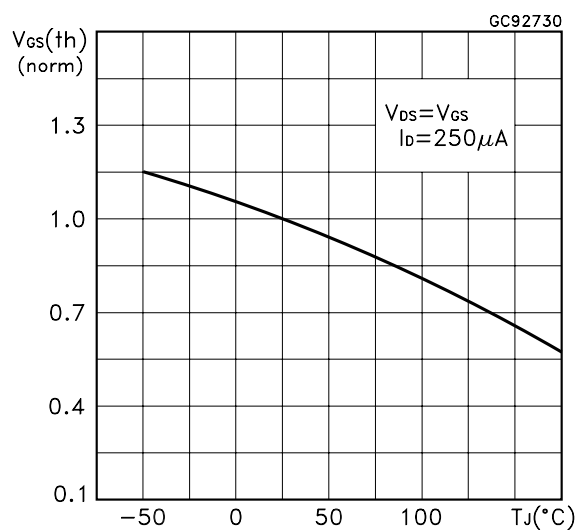
Gate Charge vs Gate-source Voltage



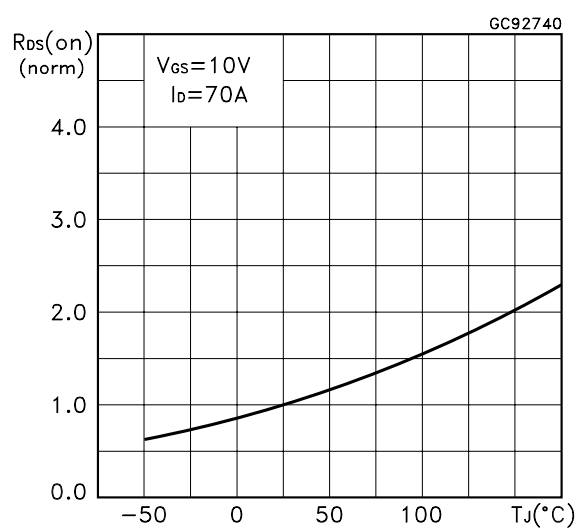
Capacitance Variations



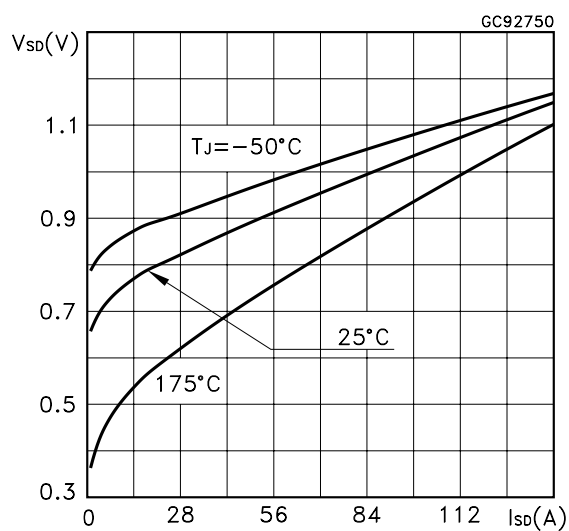
Normalized Gate Threshold Voltage vs Temperature



Normalized on Resistance vs Temperature



Source-drain Diode Forward Characteristics



Normalized Breakdown Voltage vs Temperature

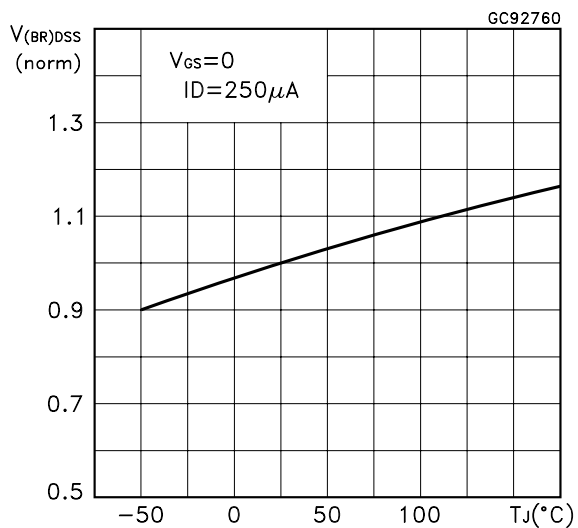


Fig. 1: Switching Times Test Circuits For Resistive Load

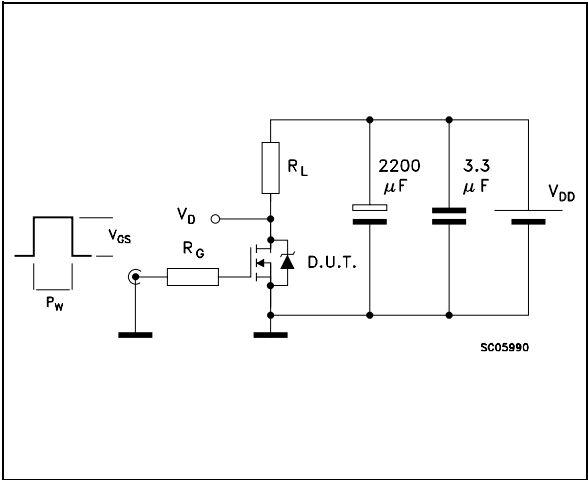


Fig. 2: Gate Charge test Circuit

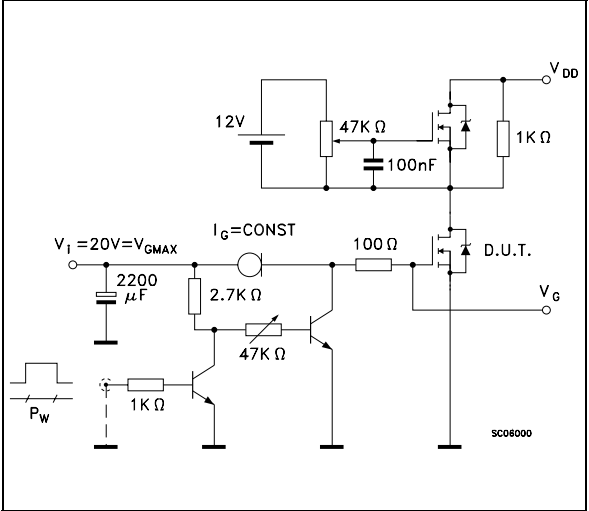
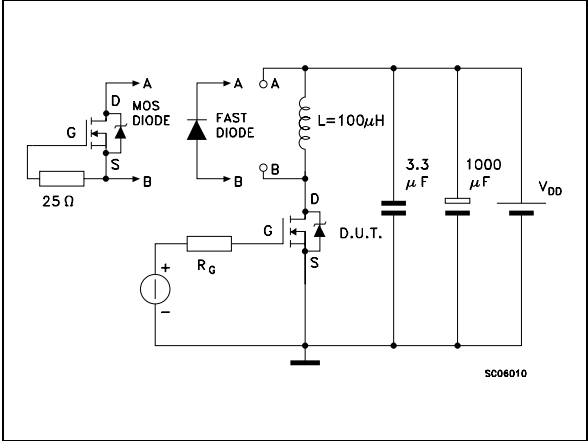
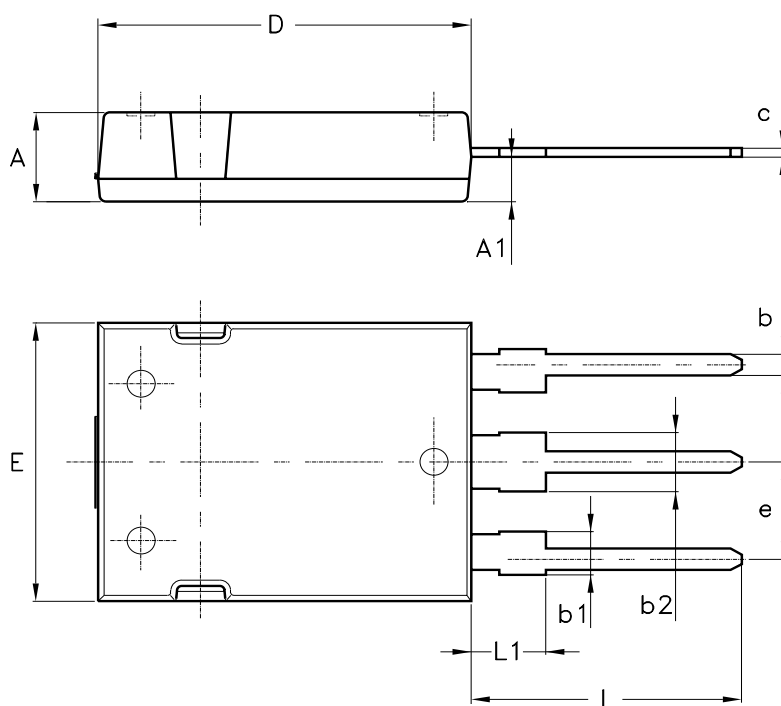


Fig. 3: Test Circuit For Diode Recovery Behaviour



Max247 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.70		5.30			
A1	2.20		2.60			
b	1.00		1.40			
b1	2.00		2.40			
b2	3.00		3.40			
c	0.40		0.80			
D	19.70		20.30			
e	5.35		5.55			
E	15.30		15.90			
L	14.20		15.20			
L1	3.70		4.30			



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